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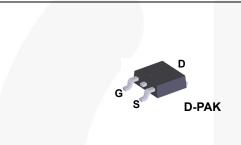
## **FQD13N10** N-Channel QFET<sup>®</sup> MOSFET 100 V, 10 A, 180 mΩ

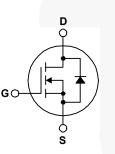
### Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce . Low Gate Charge (Typ. 12 nC) on-state resistance, and to provide superior switching • Low Crss (Typ. 20 pF) performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, • 100% Avalanche Tested audio amplifier, DC motor control, and variable switching power applications.

#### Features

- 10 A, 100 V,  $R_{DS(on)}$  = 180 m $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, I<sub>D</sub> = 5 A





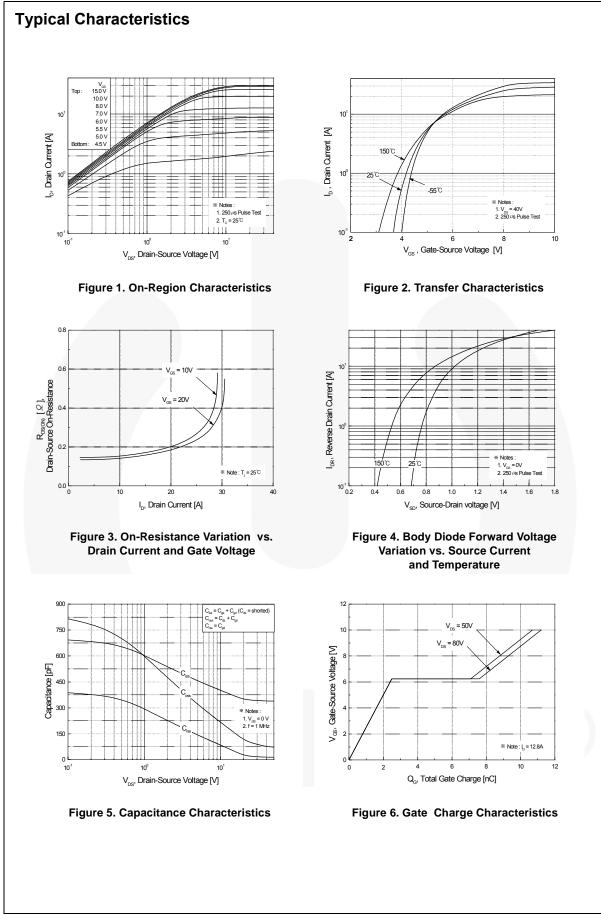
#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

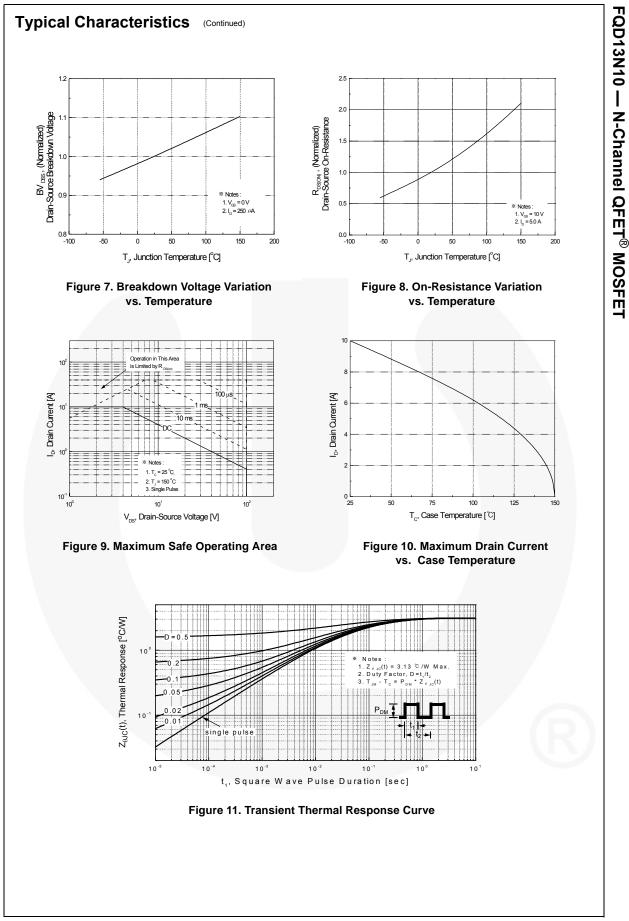
Symbol	Parameter	FQD13N10TM	Unit
V <sub>DSS</sub>	Drain-Source Voltage	100	V
I <sub>D</sub>	Drain Current - Continuous ( $T_C = 25^{\circ}C$ )	10	A
	- Continuous (T <sub>C</sub> = 100°C)	6.3	A
I <sub>DM</sub>	Drain Current - Pulsed (N	ote 1) 40	А
V <sub>GSS</sub>	Gate-Source Voltage	± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (N	ote 2) 95	mJ
I <sub>AR</sub>	Avalanche Current (N	ote 1) 10	A
E <sub>AR</sub>	Repetitive Avalanche Energy (N	ote 1) 4.0	mJ
dv/dt	Peak Diode Recovery dv/dt (N	ote 3) 6.0	V/ns
P <sub>D</sub>	Power Dissipation ( $T_A = 25^{\circ}C$ ) *	= 25°C) * 2.5	
	Power Dissipation (T <sub>C</sub> = 25°C)	40	W
	- Derate above 25°C	0.32	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
ΤL	Maximum lead temperature for soldering, .1/8" from case for 5 seconds	300	°C

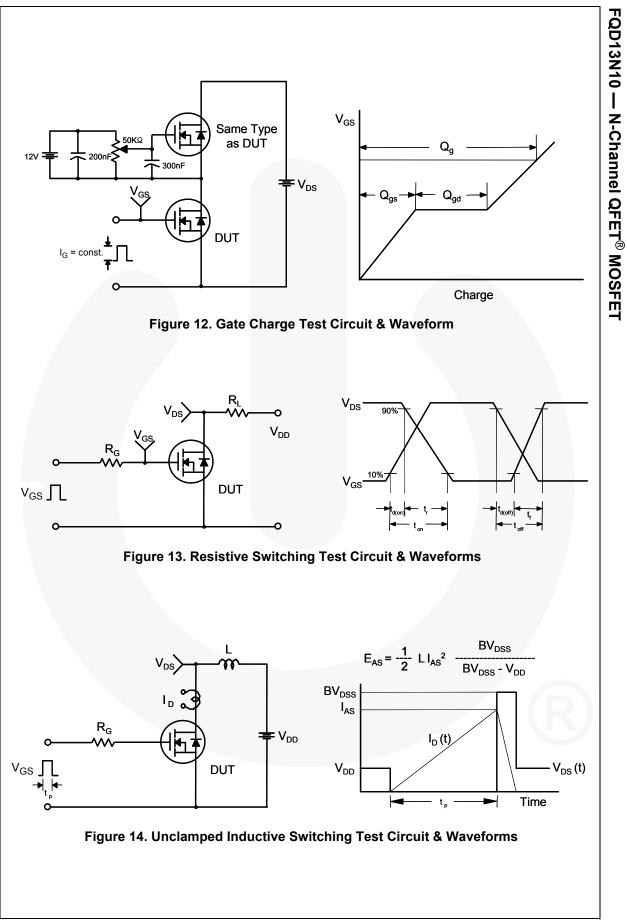
## **Thermal Characteristics**

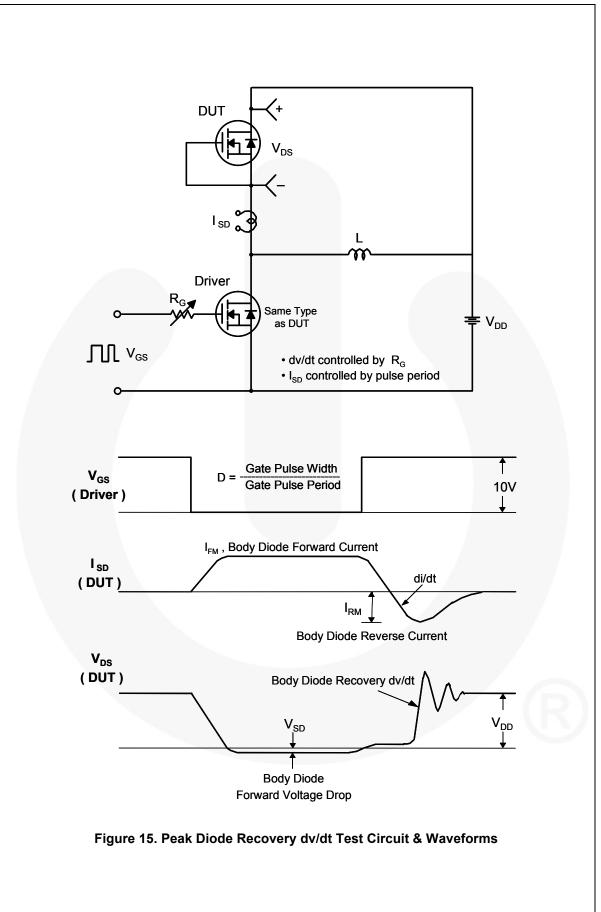
Symbol	Parameter	FQD13N10TM	Unit
$R_{\thetaJC}$	Thermal Resistance, Junction to Case, Max.	3.13	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	50	

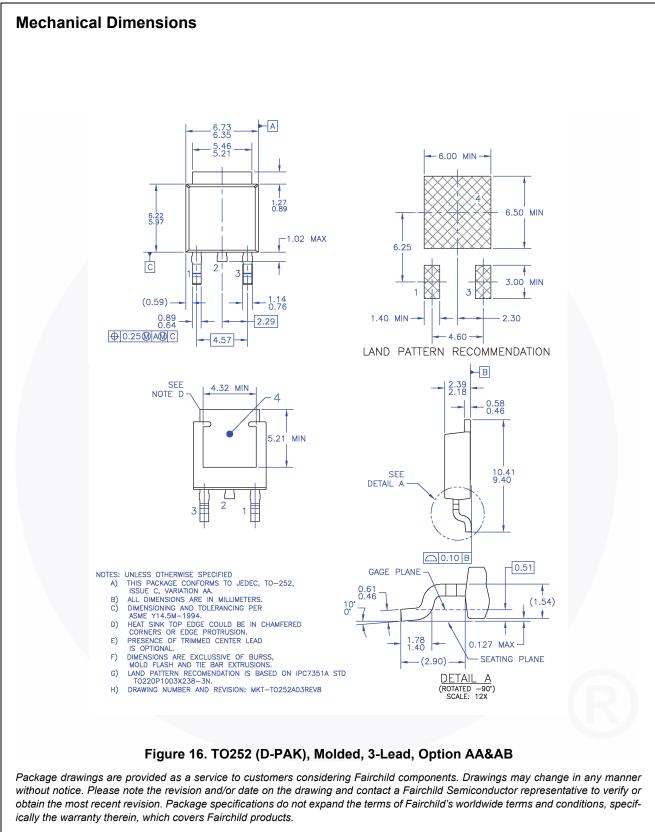
<b>lectric</b> Symbol Off Cha SV <sub>DSS</sub> ABV <sub>DSS</sub>		FQD13N10		\aye	Fackin	kage Packing Method Reel		Size	Tape W	lath	Quantity
Symbol Off Cha <sup>3V<sub>DSS</sub> ABV<sub>DSS</sub></sup>	cal Chai		-				330	mm	16 mm		2500 units
Symbol Off Cha <sup>3V<sub>DSS</sub> ABV<sub>DSS</sub></sup>	cal Cha										
Dff Cha BV <sub>DSS</sub> ABV <sub>DSS</sub>		racteristics	T <sub>C</sub> = 25°0	C unless oth	herwise noted						
BV <sub>DSS</sub>		Parameter			Test Co	nditions		Min	Тур	Мах	Unit
BV <sub>DSS</sub>	aracterist	ics									
ΔBV <sub>DSS</sub> /ΔTJ	Drain-Source Breakdown Voltage			V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA			100			V	
iΔiJ	Coefficient			$I_D$ = 250 µA, Referenced to 25°C				0.09	0.09	V/°C	
DSS	7			V <sub>DS</sub> =	V <sub>DS</sub> = 100 V, V <sub>GS</sub> = 0 V					1	μA
	Zero Gate	Voltage Drain Curr	rent	V <sub>DS</sub> =	80 V, T <sub>C</sub> =	125°C				10 100	μA
GSSF	Gate-Body	y Leakage Current,	Forward	V <sub>GS</sub> =	25 V, V <sub>DS</sub>	= 0 V					nA
GSSR	Gate-Body	y Leakage Current,	Reverse	V <sub>GS</sub> =	-25 V, V <sub>DS</sub>	<sub>s</sub> = 0 V				-100	nA
	aracteristi			1							-1
/ <sub>GS(th)</sub>		shold Voltage		V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = 1	250 µA		2.0		4.0	V
R <sub>DS(on)</sub>	Static Drai			V <sub>GS</sub> =	10 V, I <sub>D</sub> =	5.0 A			0.142	0.18	Ω
	On-Resista		_	V -	40 V, I <sub>D</sub> =	500	_		6.2		S
FS	Forward I	ransconductance	_	VDS -	40 V, I <sub>D</sub> -	5.0 A	_		6.3		3
Dvnami	ic Charac	teristics									
Ciss	Input Capa		_	V -	25 \/ \/	- 0.1/			345	450	pF
Coss	· · ·	Output Capacitance			25 V, V <sub>GS</sub> мн <del>7</del>	= 0 V,			100	130	pF
	Reverse Transfer Capacitance			f = 1.0 MHz							
2 <sub>rss</sub>	ILEVEISE I		C I						20	25	pF
Prss	Treverse I	1							20	25	pF
		acteristics							20	25	pF
Switchi		acteristics		Voo =	50 V In =	12.8 Δ			20 5	25 20	pF ns
Switchi	ing Chara	acteristics Delay Time			50 V, I <sub>D</sub> =	12.8 A,					
<b>Switchi</b> d(on) r	ing Chara Turn-On D	acteristics Delay Time Rise Time		V <sub>DD</sub> = R <sub>G</sub> = 2	5				5	20	ns
Switchi d(on) r d(off) f	<b>ing Chara</b> Turn-On D Turn-On R	acteristics Delay Time Rise Time Delay Time			5		(Note 4)		5 55	20 120	ns
Switchi d(on) r d(off) f	ing Chara Turn-On D Turn-On R Turn-Off D	acteristics Delay Time Rise Time Delay Time Call Time		R <sub>G</sub> = 2	5	(	(Note 4)		5 55 20	20 120 50	ns ns ns
C <sub>rss</sub> Switchi d(on) r d(off) f Q <sub>g</sub> Q <sub>gs</sub>	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate	acteristics Delay Time Rise Time Delay Time Call Time		R <sub>G</sub> = 2	25 Ω 80 V, I <sub>D</sub> =	(	(Note 4)		5 55 20 25	20 120 50 60	ns ns ns ns
Switchi d(on) r d(off) f Q <sub>g</sub>	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate	acteristics Delay Time Rise Time Delay Time Call Time Charge Tree Charge		R <sub>G</sub> = 2	25 Ω 80 V, I <sub>D</sub> =	( 12.8 A,	(Note 4)		5 55 20 25 12	20 120 50 60	ns ns ns ns nC
Switchi d(on) r d(off) f $\lambda_g$ $\lambda_{gs}$ $\lambda_{gd}$	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain	acteristics Delay Time Rise Time Delay Time Call Time Charge Charge n Charge		R <sub>G</sub> = 2 V <sub>DS</sub> = V <sub>GS</sub> =	25 Ω 80 V, I <sub>D</sub> = 10 V	( 12.8 A, (			5 55 20 25 12 2.5	20 120 50 60 16 	ns ns ns ns nC nC
Switchi d(on) r d(off) f Qg Qgs Qgd Drain-S	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain	Acteristics Delay Time Rise Time Delay Time Call Time Charge rce Charge n Charge ode Character	istics a	$R_G = 2$ $V_{DS} =$ $V_{GS} =$	25 Ω 80 V, I <sub>D</sub> = 10 V kimum F	12.8 A, () Ratings			5 55 20 25 12 2.5	20 120 50 60 16  	ns ns ns ns nC nC
Switchi d(on) r d(off) f 2g 2gs 2gd Drain-S s	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Dia	Acteristics Delay Time Rise Time Delay Time all Time Charge Charge n Charge ode Character Continuous Drain-S	istics al	$R_G = 2$ $V_{DS} =$ $V_{GS} =$ <b>nd Max</b>	25 Ω 80 V, $I_D =$ 10 V kimum F vard Curre	12.8 A, () Ratings			5 55 20 25 12 2.5	20 120 50 60 16   10	ns ns ns nC nC nC A
Switchi d(on) r d(off) f Q <sub>g</sub> Q <sub>gs</sub> Q <sub>gd</sub> Drain-S s SM	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Dia Maximum Maximum	acteristics Delay Time Rise Time Delay Time a Charge Charge Tree Charge n Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source	istics ar Source Dic ce Diode F	R <sub>G</sub> = 2 V <sub>DS</sub> = V <sub>GS</sub> = Md Max	$P_{25 \Omega}$ 80 V, I <sub>D</sub> = 10 V kimum F vard Current	( 12.8 A, ( <b>Ratings</b> nt		    	5 55 20 25 12 2.5 5.1	20 120 50 60 16    10 40	ns ns ns nC nC nC A A
Switchi	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Did Maximum Maximum Drain-Sou	acteristics Delay Time Rise Time Delay Time Gall Time Charge Charge Charge Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source rce Diode Forward	istics ar Source Dic ce Diode F	$R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$ $M_{GS} =$	$80 \text{ V, } \text{I}_{\text{D}} =$ $80 \text{ V, } \text{I}_{\text{D}} =$ $10 \text{ V}$ $\frac{\text{kimum F}}{\text{vard Current}}$ $\frac{\text{Current}}{0 \text{ V, } \text{I}_{\text{S}} = 1$	( 12.8 A, ( Ratings nt 0 A			5 55 20 25 12 2.5 5.1	20 120 50 60 16   10	ns ns ns nC nC nC A A A V
Switchi d(on) r d(off) f $\Omega_g$ $\Omega_{gs}$ $\Omega_{gd}$	ing Chara Turn-On D Turn-On R Turn-Off D Turn-Off F Total Gate Gate-Sour Gate-Drain Source Did Maximum Maximum Drain-Sou Reverse R	acteristics Delay Time Rise Time Delay Time a Charge Charge Tree Charge n Charge Ode Characteri Continuous Drain-S Pulsed Drain-Source	istics ar Source Dic ce Diode F	$R_{G} = 2$ $V_{DS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$ $V_{GS} =$	$P_{25 \Omega}$ 80 V, I <sub>D</sub> = 10 V kimum F vard Current	12.8 A, () Ratings nt 0 A 2.8 A,			5 55 20 25 12 2.5 5.1	20 120 50 60 16    10 40	ns ns ns nC nC nC A A











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FQD13N10 — N-Channel QFET<sup>®</sup> MOSFET



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Rev. 166

QD13N10

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